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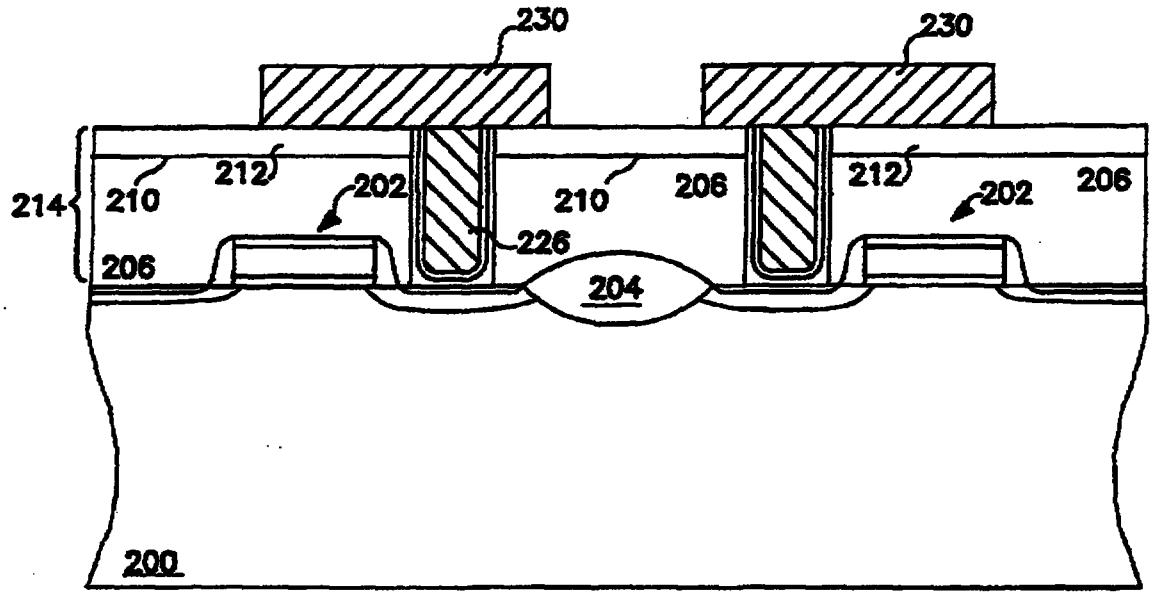
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(57) Abstract

A method of forming a novel high density interconnection structure. According to the present invention, first an insulating layer (206) is formed over a semiconductor substrate. The first insulating layer is then planarized. Next, a second insulating layer (212) is formed above the first planarized insulating layer. An opening is then etched through the first and second insulating layers. A conductive material (226) is then deposited into the opening and onto the top surface of the second insulating layer. Next, the conductive material is polished back from the second insulating layer so as to form a conductively filled opening which is substantially planar with the second insulating layer.